# ANALOG DEVICES 

## FEATURES

Isolated high－side and low－side outputs
High－side or low－side relative to input：$\pm \mathbf{7 0 0} \mathrm{V}_{\text {PEAK }}$
High－side／low－side differential： 700 V PEAK

## 0．1 A peak output current

High frequency operation： 5 MHz max
High common－mode transient immunity：$>50 \mathrm{kV} / \mu \mathrm{s}$
High temperature operation： $105^{\circ} \mathrm{C}$
Wide body，16－lead SOIC
UL1577 2500 V rms input－to－output withstand voltage

## APPLICATIONS

Isolated IGBT／MOSFET gate drives
Plasma displays
Industrial inverters
Switching power supplies

## GENERAL DESCRIPTION

The ADuM1230 ${ }^{1}$ is an isolated half－bridge gate driver that employs Analog Devices＇$i$ Coupler ${ }^{\oplus}$ technology to provide independent and isolated high－side and low－side outputs． Combining high speed CMOS and monolithic transformer technology，this isolation component provides outstanding performance characteristics superior to optocoupler－based solutions．

By avoiding the use of LEDs and photodiodes，this $i$ Coupler gate drive device is able to provide precision timing characteristics not possible with optocouplers．Furthermore，the reliability and performance stability problems associated with optocoupler LEDs are avoided．

In comparison to gate drivers employing high voltage level translation methodologies，the ADuM1230 offers the benefit of true，galvanic isolation between the input and each output．Each output may be operated up to $\pm 700 \mathrm{~V}_{\mathrm{p}}$ relative to the input， thereby supporting low－side switching to negative voltages．The differential voltage between the high－side and low－side can be as high as $700 \mathrm{~V}_{\mathrm{P}}$ ．

As a result，the ADuM1230 provides reliable control over the switching characteristics of IGBT／MOSFET configurations over a wide range of positive or negative switching voltages．

FUNCTIONAL BLOCK DIAGRAM


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## REVISION HISTORY

11/05—Rev. Sp0 to Rev. A

5/05—Revision Sp0: Initial Version

## SPECIFICATIONS

## ELECTRICAL CHARACTERISTICS

All voltages are relative to their respective ground. $4.5 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DDI}} \leq 5.5 \mathrm{~V}, 12 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DDA}} \leq 18 \mathrm{~V}, 12 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DDB}} \leq 18 \mathrm{~V}$. All min/max specifications apply over the entire recommended operating range, unless otherwise noted. All typical specifications are at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, $\mathrm{V}_{\mathrm{DDI}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{DDA}}=15 \mathrm{~V}, \mathrm{~V}_{\mathrm{DDB}}=15 \mathrm{~V}$.

Table 1.

| Parameter | Symbol | Min | Typ | Max | Unit | Test Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DC SPECIFICATIONS |  |  |  |  |  |  |
| Input Supply Current, Quiescent | $\mathrm{IDDI}(0)$ |  |  | 4.0 | mA |  |
| Output Supply Current, A or B, Quiescent | IDDA (Q), IDDB (Q) |  |  | 1.2 | mA |  |
| Input Supply Current, 10 Mbps | IDDI (10) |  |  | 8.0 | mA |  |
| Output Supply Current, A or B, 10 Mbps | IDDA (10), IdDB (10) |  |  | 22 | mA | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Input Currents | $\mathrm{IIA}^{\text {, İB, }}$, ILISABLE | -10 | +0.01 | +10 | $\mu \mathrm{A}$ | $0 \leq \mathrm{V}_{\text {IA }}, \mathrm{V}_{\text {IB }}, \mathrm{V}_{\text {DISABLE }} \leq \mathrm{V}_{\text {DD } 1}$ |
| Logic High Input Threshold | $\mathrm{V}_{\mathrm{IH}}$ | 2.0 |  |  | V |  |
| Logic Low Input Threshold | $\mathrm{V}_{\text {IL }}$ |  |  | 0.8 | V |  |
| Logic High Output Voltages | Vоан, Vовн | $\begin{aligned} & V_{D D A}-0.1, \\ & V_{D D B}-0.1 \end{aligned}$ | $V_{\text {DDA }}, V_{\text {dib }}$ |  | V | $\mathrm{I}_{\text {OA, }} \mathrm{I}_{\mathrm{O}}=-1 \mathrm{~mA}$ |
| Logic Low Output Voltages | $\mathrm{V}_{\text {oal }} \mathrm{V}$ Vobl |  |  | 0.1 | V | $\mathrm{I}_{\mathrm{OA}}, \mathrm{l}_{\text {Ob }}=1 \mathrm{~mA}$ |
| Output Short-Circuit Pulsed Current ${ }^{1}$ | $\mathrm{loa} \mathrm{(SC)}, \mathrm{lob}_{\text {(SC) }}$ | 100 |  |  | mA |  |
| SWITCHING SPECIFICATIONS |  |  |  |  |  |  |
| Minimum Pulse Width ${ }^{2}$ | PW |  |  | 100 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Maximum Switching Frequency ${ }^{3}$ |  | 10 |  |  | Mbps | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Propagation Delay ${ }^{4}$ | $\mathrm{t}_{\text {PHL, }} \mathrm{t}_{\text {PLH }}$ | 97 | 124 | 160 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Change vs. Temperature |  |  | 100 |  | $\mathrm{ps} /{ }^{\circ} \mathrm{C}$ |  |
| Pulse Width Distortion, $\left\|t_{\text {PLH }}-t_{\text {PHL }}\right\|$ | PWD |  |  | 8 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Channel-to-Channel Matching, Rising or Falling Edges ${ }^{5}$ |  |  |  | 5 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Channel-to-Channel Matching, Rising vs. Falling Edges ${ }^{6}$ |  |  |  | 13 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Part-to-Part Matching, Rising or Falling Edges ${ }^{7}$ |  |  |  | 55 | ns | $\mathrm{CL}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Part-to-Part Matching, Rising vs. Falling Edges ${ }^{8}$ |  |  |  | 63 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |
| Output Rise/Fall Time (10\% to 90\%) | $\mathrm{t}_{\mathrm{R}} / \mathrm{t}_{\mathrm{F}}$ |  |  | 20 | ns | $\mathrm{C}_{\mathrm{L}}=200 \mathrm{pF}$ |

[^0]
## PACKAGE CHARACTERISTICS

Table 2.

| Parameter | Symbol | Min | Typ | Max | Unit | Test Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Resistance (Input-to-Output) ${ }^{1}$ | R-O |  | $10^{12}$ |  | $\Omega$ |  |
| Capacitance (Input-to-Output) ${ }^{1}$ | $\mathrm{Cl}_{1-\mathrm{O}}$ |  | 2.0 |  | pF | $\mathrm{f}=1 \mathrm{MHz}$ |
| Input Capacitance | $C_{1}$ |  | 4.0 |  | pF |  |
| IC Junction-to-Ambient Thermal Resistance | $\theta_{\text {Jсa }}$ |  | 76 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |  |

${ }^{1}$ The device is considered a 2-terminal device: Pins 1 through 8 are shorted together, and Pins 9 through 16 are shorted together.

## REGULATORY INFORMATION

The ADuM1230 is approved, as shown in Table 3.
Table 3.

| UL'$^{1}$ |
| :--- |
| Recognized under 1577 component recognition program |
| 'In accordance with UL1577, each ADuM1230 is proof tested by applying an insulation test voltage $\geq 3000 \mathrm{~V}$ rms for 1 second (current leakage detection limit $=5 \mu \mathrm{~A})$. |

## INSULATION AND SAFETY-RELATED SPECIFICATIONS

Table 4.

| Parameter | Symbol | Value | Unit | Conditions |
| :---: | :---: | :---: | :---: | :---: |
| Rated Dielectric Insulation Voltage |  | 2500 | V rms | 1 minute duration |
| Minimum External Air Gap (Clearance) | L(101) | 7.7 min | mm | Measured from input terminals to output terminals, shortest distance through air |
| Minimum External Tracking (Creepage) | L(102) | 8.1 min | mm | Measured from input terminals to output terminals, shortest distance path along body |
| Minimum Internal Gap (Internal Clearance) |  | 0.017 min | mm | Insulation distance through insulation |
| Tracking Resistance (Comparative Tracking Index) | CTI | >175 | V | DIN IEC 112/VDE 0303 Part 1 |
| Isolation Group |  | Illa |  | Material Group (DIN VDE 0110, 1/89, Table 1) |

## RECOMMENDED OPERATING CONDITIONS

Table 5.

| Parameter | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Operating Temperature | $\mathrm{T}_{\text {A }}$ | -40 | +105 | ${ }^{\circ} \mathrm{C}$ |
| Input Supply Voltage ${ }^{1}$ | $V_{\text {DD1 }}$ | 4.5 | 5.5 | V |
| Output Supply Voltages ${ }^{1}$ | $V_{\text {DDA }}, V_{\text {DDB }}$ | 12 | 18 | V |
| Input Signal Rise and Fall Times |  |  | 1 | ms |
| Common-Mode Transient Immunity, Input-to-Output ${ }^{2}$ |  | -50 | +50 | kV/ $\mu \mathrm{s}$ |
| Common-Mode Transient Immunity, Between Outputs ${ }^{2}$ |  | -50 | +50 | kV/ $/ \mathrm{s}$ |
| Transient Immunity, Supply Voltages ${ }^{2}$ |  | -50 | +50 | kV/ $/ \mathrm{s}$ |

[^1]
## ABSOLUTE MAXIMUM RATINGS

Table 6.

| Parameter | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Storage Temperature | $\mathrm{T}_{\text {st }}$ | -55 | +150 | ${ }^{\circ} \mathrm{C}$ |
| Ambient Operating Temperature | $\mathrm{T}_{\text {A }}$ | -40 | +105 | ${ }^{\circ} \mathrm{C}$ |
| Input Supply Voltage ${ }^{1}$ | $\mathrm{V}_{\mathrm{DD} 1}$ | -0.5 | +7.0 | V |
| Output Supply Voltage ${ }^{1}$ | $V_{\text {DDA }}, V_{\text {DDB }}$ | -0.5 | +27 | V |
| Input Voltage ${ }^{1}$ | $V^{1 A}, V_{\text {IB }}$ | -0.5 | $\mathrm{V}_{\text {DII }}+0.5$ | V |
| Output Voltage ${ }^{1}$ | $V_{\text {oa }}, V_{\text {Ob }}$ | -0.5 | $\begin{aligned} & V_{D D A}+0.5, \\ & V_{D D B}+0.5 \end{aligned}$ | V |
| Input-Output Voltage ${ }^{2}$ |  | -700 | +700 | $V_{\text {peak }}$ |
| Output Differential Voltage ${ }^{3}$ |  |  | 700 | $V_{\text {PEAK }}$ |
| Output DC Current | Ioa, lob | -20 | +20 | mA |
| Common-Mode Transients ${ }^{4}$ |  | -100 | +100 | kV/ $\mu \mathrm{s}$ |

${ }^{1}$ All voltages are relative to their respective ground.
${ }^{2}$ Input-to-output voltage is defined as $\mathrm{GND}_{\mathrm{A}}-\mathrm{GND}_{1}$ or $\mathrm{GND}_{\mathrm{B}}-\mathrm{GND}_{1}$.
${ }^{3}$ Output differential voltage is defined as $\mathrm{GND}_{\mathrm{A}}-\mathrm{GND}_{\mathrm{B}}$.
${ }^{4}$ Refers to common-mode transients across any insulation barrier. Commonmode transients exceeding the Absolute Maximum Ratings can cause latchup or permanent damage.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Ambient temperature $=25^{\circ} \mathrm{C}$, unless otherwise noted.

Table 7. ADuM1230 Truth Table (Positive Logic)

| $\mathrm{V}_{\mathrm{IA}} / \mathrm{V}_{\text {IB }}$ Input | VDD1 State | DISABLE | V ${ }_{\text {oA }} / \mathrm{V}_{\text {OB }}$ Output | Notes |
| :---: | :---: | :---: | :---: | :---: |
| H | Powered | L | H |  |
| L | Powered | L | L |  |
| X | Unpowered | X | L | Output returns to input state within $1 \mu$ of $V_{\text {DDI }}$ power restoration. |
| X | Powered | H | L |  |

## ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on

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[^0]:    ${ }^{1}$ Short-circuit duration less than 1 second. Average power must conform to the limit shown under the Absolute Maximum Ratings.
    ${ }^{2}$ The minimum pulse width is the shortest pulse width at which the specified timing parameters are guaranteed.
    ${ }^{3}$ The maximum switching frequency is the maximum signal frequency at which the specified timing parameters are guaranteed.
    ${ }^{4} \mathrm{t}_{\text {рнL }}$ propagation delay is measured from the $50 \%$ level of the falling edge of the $\mathrm{V}_{1 \times}$ signal to the $50 \%$ level of the falling edge of the $\mathrm{V}_{\text {ox }}$ signal. $\mathrm{t}_{\text {рнн }}$ propagation delay is measured from the $50 \%$ level of the rising edge of the $V_{1 x}$ signal to the $50 \%$ level of the rising edge of the $V_{\text {ox }}$ signal.
    ${ }^{5}$ Channel-to-channel matching, rising vs. falling edges is the magnitude of the propagation delay difference between two channels of the same part when the inputs are either both rising edges or falling edges. The supply voltages and the loads on each channel are equal.
    ${ }^{6}$ Channel-to-channel matching, rising or falling edges is the magnitude of the propagation delay difference between two channels of the same part when one input is a rising edge and the other input is a falling edge. The supply voltages and loads on each channel are equal.
    ${ }^{7}$ Part-to-part matching, rising or falling edges is the magnitude of the propagation delay difference between the same channels of two different parts when the inputs are either both rising or falling edges. The supply voltages, temperatures, and loads of each part are equal.
    ${ }^{8}$ Part-to-part matching, rising vs. falling edges is the magnitude of the propagation delay difference between the same channels of two different parts when one input is a rising edge and the other input is a falling edge. The supply voltages, temperatures, and loads of each part are equal.

[^1]:    ${ }^{1}$ All voltages are relative to their respective ground.
    ${ }^{2}$ See the Common-Mode Transient Immunity section for transient diagrams and additional information.

